

**REMARKS**

This Preliminary Amendment is being submitted with a Request for Continued Examination (RCE),

Claims 4-10, 14-22, and 25-28 have been canceled without prejudice or disclaimer of their subject matter, and claims 29-35 have been newly presented. Thus, claims 29-35 are pending in the application.

The Request for Continued Examination (RCE) has been submitted for the sake of expediency and should not be construed as acquiescing to the Examiner's rejection of the claims contained in the 13 January 2006 Final Office Action.

More particularly, it is submitted that the present claims are patentable over the cited art, taken either alone or in combination, for the following reasons:

Arai *et al.*, U.S. Patent No. 6,160,272 does not disclose the orderly stacked structures of the present invention (Ti/TiN/Al based metal/TiN/Ti, and Ti/diffusion prevention layer/Al based metal/diffusion prevention layer/Ti). Arai *et al.* '272 only discloses that a lower layer line of a TFT of a prior art should have various properties, and to content this properties, the lower layer line is formed of TiN containing equal to or less than 50 atm% of Ni. Furthermore, Yaegashi *et al.*, Japanese Patent Publication No. 2002-026335 also does not disclose an orderly stacked structure of Ti/TiN/Al based metal/TiN/Ti and an orderly stacked structure of Ti/diffusion prevention layer/Al based metal/diffusion prevention layer/Ti. The Yaegashi *et al.*

'335 reference only discloses a gate electrode 32b, an orderly stacked structure of an Al layer 33a/ an AlOx layer 33b/ a Ti layer 33c, and source/drain electrodes 38b, 38c formed on ohmic contact layers 37 which are contacted with an active. Finally, the stacked structure of Takahisa *et al.*, Japanese Patent Publication No. 07-058110 is not the same as the stacked structure of the present invention of Ti/TiN/Al based metal/TiN/Ti and Ti/diffusion prevention layer/Al based metal/ diffusion prevention layer /Ti. Takahisa *et al.* '110 only discloses source/drain electrodes respectively having an orderly stacked structure of Ti/TiON/Al alloy/Ti/TiN.

Furthermore, in connection with the Yaegashi *et al.* '335 reference, the reference numeral 33a is an Al layer, the reference numeral 33b is an AlOx layer, and the reference numeral 33c is a Ti layer. Yaegashi *et al.* '335 does not disclose the first and second Ti layers, the first and second TiN layers, and the aluminum-based metal layer.

Still furthermore, in connection with the Arai *et al.* '272 reference, the reference numeral 108a is an upper side layer, and the reference numeral 108b is a lower side layer. The upper side layer 108a is a titanium nitride, and the lower side layer 108b is a high melting point metal having low resistance. In Arai *et al.* '272, the lower side layer 108b of the high melting point metal having low resistance is contacted with a semiconductor layer 107 and the upper side layer 108a is contacted with a transparent electrode 113. Thus, Yaegashi *et al.* '335 does not disclose the first and second Ti layers, the first and second TiN layers, and the aluminum-based metal layer of the present invention.

Finally, in connection with the Takahisa *et al.* '110 reference, a portion of source/drain

electrodes contacted with another conductive layer 20 is a TiN layer 16e. Thus, Takahisa *et al.* '110 does not disclose the structure of the present invention.

In view of the foregoing arguments and remarks, all claims are deemed to be allowable and this application is believed to be in condition to be passed to issue. Should any questions remain unresolved, the Examiner is requested to telephone Applicants' attorney.

Fees for filing a Request for Continued Examination (RCE) and for a Petition for a three-month extension of time accompany this Preliminary Amendment. Should the check become lost, be deficient in payment, or should other fees be incurred, the Commissioner is authorized to charge Deposit Account No. 02-4943 of Applicant's undersigned attorney in the amount of such fees.

Respectfully submitted,



Robert E. Bushnell,  
Attorney for the Applicant  
Registration No.: 27,774

1522 "K" Street N. W.,  
Suite 300  
Washington, D.C. 20005  
(202) 408-9040

Folio: P57001  
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I.D.: REB/HMZ